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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/712,323	11/14/2003	Koichi Kaneko	OKI 381	1976
23995 7:	590 06/28/2004		EXAMINER	
RABIN & Berdo, PC			ESTRADA, MICHELLE	
1101 14TH ST SUITE 500	REET, NW	ART UNIT	PAPER NUMBER	
WASHINGTON, DC 20005			2823	-
			DATE MAILED: 06/28/200	4

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Appli	cation No.	Applicant(s)	-		
Office Action Summary		10/7	12,323	KANEKO, KOICHI			
		Exan	nin r	Art Unit			
			elle Estrada	2823			
The MAIL Period for Reply	ING DATE of this commu	nication appears o	n the cover sheet w	ith the correspondence addr	ess		
THE MAILING C - Extensions of time n after SIX (6) MONTH - If the period for reply - If NO period for reply - Failure to reply withi Any reply received b	STATUTORY PERIOD IN PATE OF THIS COMMUNITY be available under the provision as from the mailing date of this come is specified above, the maximum so the set or extended period for reply the Office later than three months adjustment. See 37 CFR 1.704(b).	IICATION. s of 37 CFR 1.136(a). In munication. 30) days, a reply within th statutory period will apply: y will, by statute, cause th	no event, however, may a e statutory minimum of thir and will expire SIX (6) MON e application to become Al	reply be timely filed ty (30) days will be considered timely. NTHS from the mailing date of this come BANDONED (35 U.S.C. § 133).	munication.		
Status							
2a)☐ This action 3)☐ Since this	This action is FINAL . 2b)⊠ This action is non-final.						
Disposition of Clai	·	noe ander Ex part	guayio, 1000 o.c	7. 11, 100 0.0. 210.			
4) Claim(s) 1 4a) Of the 5) Claim(s) 1 6) Claim(s) 1 7) Claim(s) 2 8) Claim(s) 2 Application Papers 9) The specification Papers Applicant management	-6 is/are pending in the a above claim(s) is/a above claim(s) is/a is/are allowed6 is/are rejected is/are objected to are subject to restruction is objected to by the ag(s) filed on is/are any not request that any object drawing sheet(s) including	are withdrawn from iction and/or election e Examiner. a: a) accepted continuous accepted of the correction is referenced to the drawing the correction is referenced.	on requirement. or b) objected to g(s) be held in abeya equired if the drawing				
Priority under 35 U	.S.C. § 119						
a)⊠ All b)[1.⊠ Cer 2.□ Cer 3.□ Cop app	gment is made of a claim Some * c) None of: tified copies of the priority tified copies of the priority ties of the certified copies lication from the Internation ached detailed Office action	y documents have y documents have s of the priority doc onal Bureau (PCT	been received. been received in Accuments have been Rule 17.2(a)).	Application No received in this National S	tage		
Attachment(s) 1) X Notice of Reference	es Cited (PTO-892)		4) 🔲 Interview	Summary (PTO-413)			
2) Notice of Draftspe	rson's Patent Drawing Review (sure Statement(s) (PTO-1449 o		Paper No	s)/Mail Date Informal Patent Application (PTO-1	152)		

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-6 are rejected under 35 U.S.C. 102(b) as being anticipated by Nagano (6,159,856).

With respect to claims 1 and 4, Nagano discloses forming a high melting-point metal layer (16) over an entire surface including over the device isolation region (12) and the first and second diffusion layers (13c/13d) and first and second MOS transistors (See fig. 13); selectively introducing a silicon element (17) into the high meting-point metal layer on the device isolation region; silicidizing by thermal treatment the high melting-point metal layer having introduced therein the silicon element on the first and second diffusion layers and the device isolation region (Col. 7, lines 38-42); and selectively removing the high melting-point metal layer to be silicidized remaining unreacted (Col. 7, lines 45-49).

With respect to claims 2 and 5, Nagano discloses wherein the high melting-point metal layer is a cobalt layer (Col. 7, line 33).

With respect to claims 3 and 6, Nagano discloses wherein said introduction is done by an ion implantation method (Col. 7, lines 35-37).

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michelle Estrada whose telephone number is 571-272-1858. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 571-272-2800.

June 23, 2004

Olik Chaudhuri Supervisory Patent Examiner **Technology Center 2800**